

## Solid State Devices, Inc.

14701 Firestone Blvd \* La Mirada, ČA 90638 Phone: (562) 404-4474 \* Fax: (562) 404-1773 ssdi@ssdi-power.com \* www.ssdi-power.com

## **Designer's Data Sheet**

Part Number/Ordering Information <sup>1</sup>/
SFS182

Screening 2/ = Not Screened TX = TX Level TXV = TXV Level S = S Level

/39 = TO-39

Package

/18 = TO-18

Voltage/Family 6 = 200V

7 = 250V

8 = 300V 9 = 400V

# SFS1826 – SFS1829 Series

# 1.6 AMP SILICON CONTROLLED RECTIFIER 200 - 400 Volts

#### **FEATURES:**

- Low-Level Gate Characteristics
- Low Holding Current I<sub>H</sub> = 5 mA (Max) @ 25°C
- Anode Common to Case
- Hermetically Sealed
- TX, TXV, S-Level Screening Available Consult Factory

MAXIMUM RATINGS <sup>3/</sup>		Symbol	Value	Units
Peak Repetitive Reverse Voltage and DC Blocking Voltage	SFS1826 SFS1827 SFS1828 SFS1829	$oldsymbol{V}_{DRM}$	200 250 300 400	Volts
Non-Repetitive Peak Reverse Blocking Voltage (t < 5.0 ms)	SFS1826 SFS1827 SFS1828 SFS1829	$V_{RSM}$	300 350 400 500	Volts
RMS On-State Current (All Conduction Angles)		I <sub>T(RMS)</sub>	1.6	Amps
Average On-State Current	$T_C = 50$ °C $T_A = 25$ °C	I <sub>T(AV)</sub>	1.0 0.7	Amps
Peak Non-Repetitive Surge Current (One Cycle, 60 Hz, T <sub>C</sub> = 80°C)		I <sub>TSM</sub>	15	Amps
Peak Gate Power		$P_{GM}$	0.1	Watts
Average Gate Power		P <sub>G(AV)</sub>	0.01	Watts
Peak Gate Current		I <sub>GM</sub>	0.1	Amps
Peak Gate Voltage		$V_{GM}$	6.0	Volts
Operating Junction Temperature Range		TJ	-65 to +200	°C
Storage Temperature Range		T <sub>stg</sub>	-65 to +200	°C
Thermal Resistance, Junction to Case		R <sub>eJC</sub>	72	°C/W

NOTES: TO-18 (/18) TO-39 (/39)

- 1/ For ordering information, price, operating curves, and availability- Contact factory.
- 2/ Screening based on MIL-PRF-19500. Screening flows available on request.
- 3/ Unless otherwise specified, all electrical characteristics @25°C,  $R_{GK}$  = 1K  $\Omega$ .
- 4/ RGK current is not included in measurement.
- 5/ Thyristor devices shall not be tested with a constant current source for forward and reverse blocking capability such that the voltage applies exceeds the rated blocking voltage.
- **6**/ Thyristor devices shall not have a positive bias applied to the gate concurrently with a negative potential applied to the anode.





NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: SCR005C

DOC

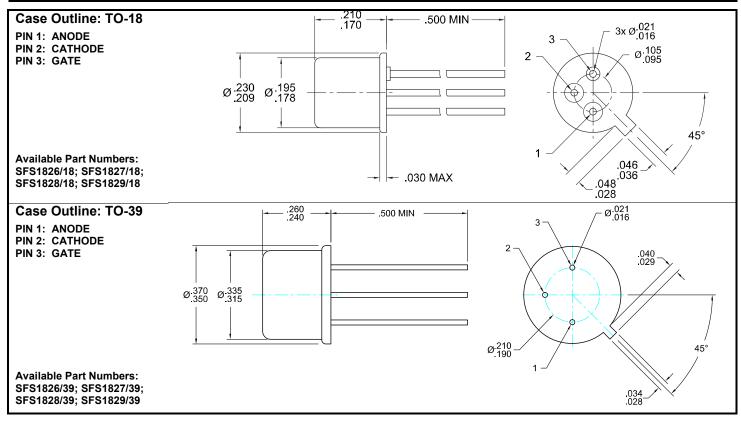


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ELECTRICAL CHARACTERISTICS3	Symbol	Min	Max	Unit
Peak Reverse Blocking Current Rated V <sub>RRM</sub>	I <sub>RRM</sub>		1	μΑ
Peak Forward Blocking Current Rated $V_{DRM}$ , $R_{GK}$ = 1K $\Omega$	I <sub>DRM</sub>		1	μΑ
Peak On-State Voltage I <sub>F</sub> = 1.6 A Peak	V <sub>TM</sub>		1.3	Volts
Gate Trigger Current $V_D = 6 V_{DC}$ , $R_L = 100 \Omega$ , $T_C = -65^{\circ}C$	I <sub>GT</sub>		350	μΑ
Gate Trigger Voltage $V_D = 6 V_{DC}$ , $R_L = 100 \Omega$ , $T_C = 25^{\circ}C$ $V_D = 6 V_{DC}$ , $R_L = 100 \Omega$ , $T_C = -65^{\circ}C$	V <sub>GT</sub>	_	0.7 0.9	Volts
Holding Current $V_D = 6 V_{DC}$ $V_D = 6 V_{DC}$ , $T_C = -65^{\circ}C$	I <sub>H</sub>		5 2.0	mA



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